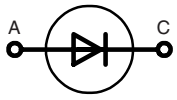
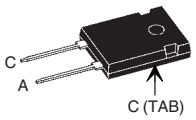
HiPerFRED™ Epitaxial Diode
with soft recovery

I_{FAV} = 30 A
V_{RRM} = 1200 V
t_{rr} = 40 ns

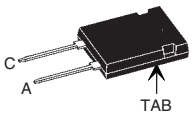
V_{RSM} V	V_{RRM} V	Type
1200	1200	DSEP 30-12A
1200	1200	DSEP 30-12AR



TO-247 AD
Version A



ISOPLUS 247™
Version AR



A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		70	A
I_{FAVM}	rectangular, d = 0.5; T_C (Vers. A) = 115°C T_C (Vers. AR)= 110°C	30	A
I_{FSM}	T_{VJ} = 45°C; t_p = 10 ms (50 Hz), sine	200	A
E_{AS}	T_{VJ} = 25°C; non-repetitive I_{AS} = 11.5 A; L = 180 µH	14	mJ
I_{AR}	$V_A = 1.25 \cdot V_R$ typ.; f = 10 kHz; repetitive	1.2	A
T_{VJ}		-55...+175	°C
T_{VJM}		175	°C
T_{stg}		-55...+150	°C
P_{tot}	T_C = 25°C	165	W
M_d *	mounting torque	0.8...1.2	Nm
F_C	mounting force with clip	20...120	N
V_{ISOL} **	50/60 Hz RMS; $I_{ISOL} \leq$ 1 mA; leads-to-tab	2500	V~
Weight	typical	6	g

* Version A only; ** Version AR only

Symbol	Conditions	Characteristic Values typ.	max.	
I_R ①	T_{VJ} = 25°C; $V_R = V_{RRM}$		250	µA
	T_{VJ} = 150°C; $V_R = V_{RRM}$		1	mA
V_F ②	I_F = 30 A; T_{VJ} = 150°C		1.79	V
	T_{VJ} = 25°C		2.74	V
R_{thJC}	Version A		0.9	K/W
	Version AR		1.1	K/W
R_{thCH}		0.25		K/W
t_{rr}	I_F = 1 A; -di/dt = 200 A/µs; V_R = 30 V; T_{VJ} = 25°C	40		ns
I_{RM}	V_R = 100 V; I_F = 50 A; $-di_F/dt$ = 100 A/µs T_{VJ} = 100°C	8.5	11.4	A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%
② Pulse Width = 300 µs, Duty Cycle < 2.0%

Data according to IEC 60747 and per diode unless otherwise specified.

Features
- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM}-values
- Soft recovery behaviour
- Epoxy meets UL 94V-0
- Version ..R isolated and UL registered E153432

Applications
- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Dimensions see Outlines.pdf

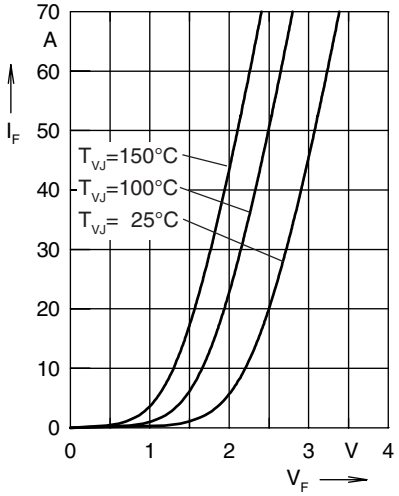


Fig. 1 Forward current I_F versus V_F

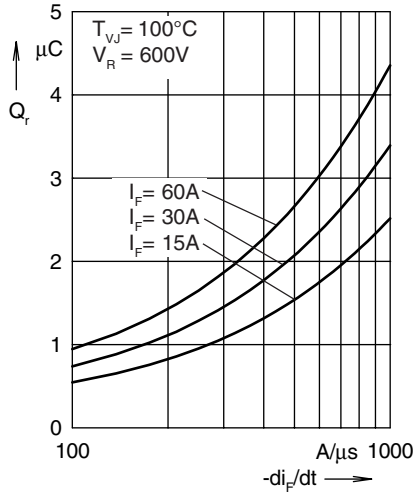


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

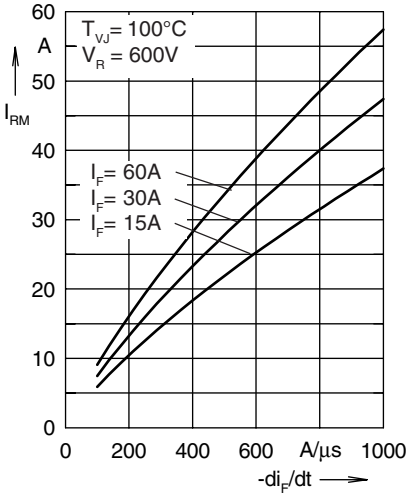


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

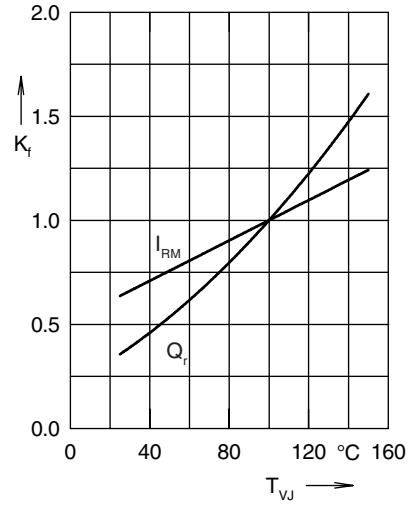


Fig. 4 Dynamic parameters Q_r, I_{RM} versus T_{VJ}

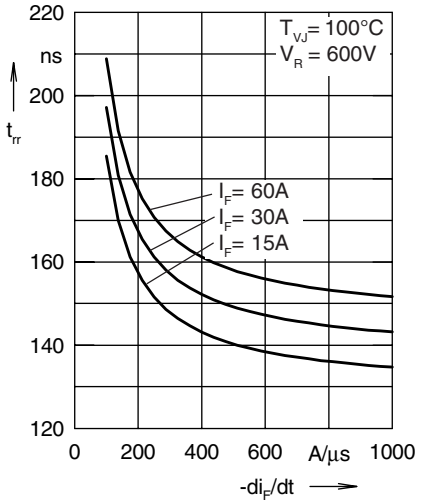


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

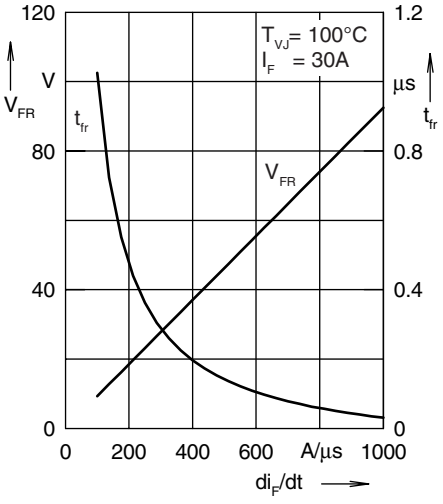


Fig. 6 Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

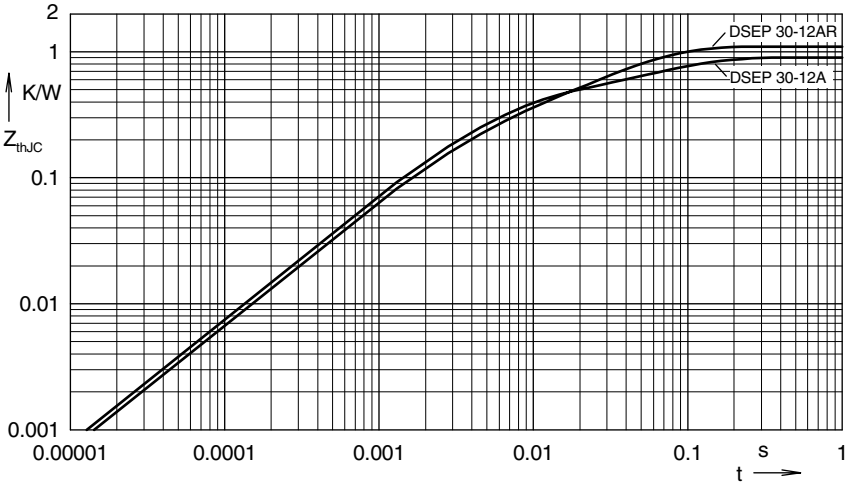


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation ..A:

i	R_{thi} (K/W)	t_i (s)
1	0.465	0.0052
2	0.179	0.0003
3	0.256	0.0397

Constants for Z_{thJC} calculation ..AR:

i	R_{thi} (K/W)	t_i (s)
1	0.368	0.0052
2	0.1417	0.0003
3	0.0295	0.0004
4	0.5604	0.0092

NOTE: Fig. 2 to Fig. 6 shows typical values